CPH3456

Power MOSFET 20V, $71m\Omega$, 3.5A, Single N-Channel



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Features

- ON-Resistance $R_{DS}(on)1=54m\Omega$ (typ)
- 1.8V Drive
- Pb-Free, Halogen Free and RoHS Compliance

Specifications

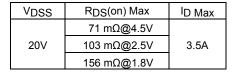
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ID	3.5	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I _{DP}	14	А
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	PD	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

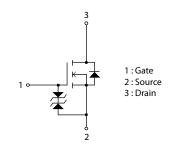
This product is designed to "ESD immunity < $200V^*$ ", so please take care when handling.

Thermal Resistance Ratings

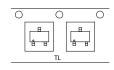
Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm²x0.8mm)	R _{θJA}	125	°C/W



Electrical Connection N-Channel



Packing Type:TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*} Machine Model

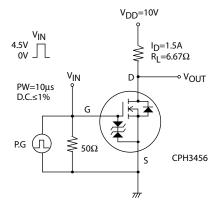
CPH3456

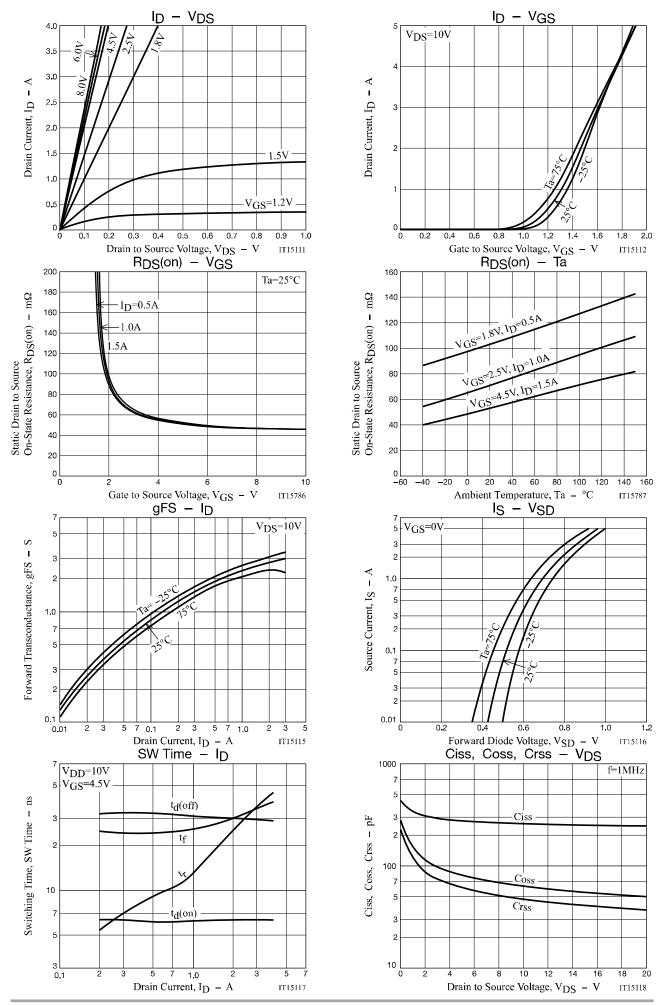
Electrical Characteristics at Ta = 25°C

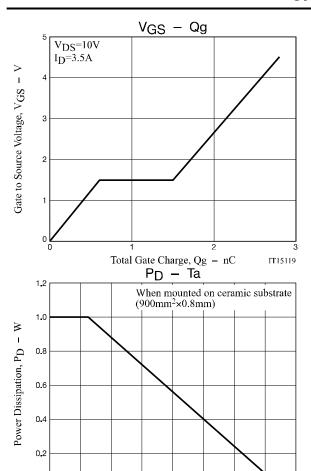
Parameter	O. male al	Conditions	Value		11.2	
Parameter	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	gFS .	V _{DS} =10V, I _D =1.5A		2.8		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =1.5A, V _{GS} =4.5V		54	71	mΩ
	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		73	103	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.8V		104	156	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		260		pF
Output Capacitance	Coss			65		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		6.2		ns
Rise Time	t _r			19		ns
Turn-OFF Delay Time	t _d (off)			30		ns
Fall Time	tf			28		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		2.8		nC
Gate to Source Charge	Qgs			0.6		nC
Gate to Drain "Miller" Charge	Qgd			0.9		nC
Forward Diode Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.85	1.2	V

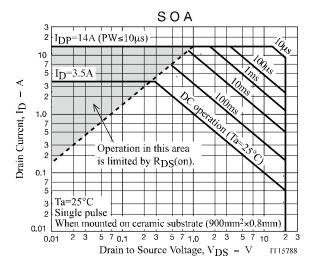
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

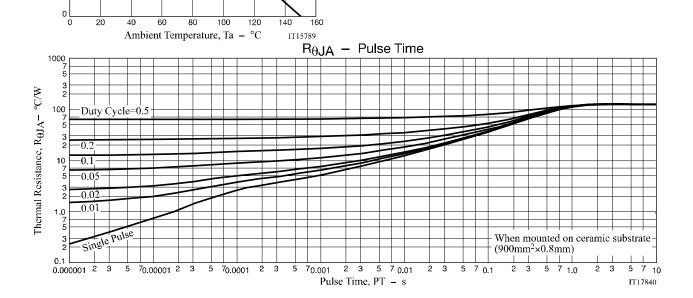
Switching Time Test Circuit











Package Dimensions

CPH3456-TL-H/ CPH3456-TL-W

CPH3

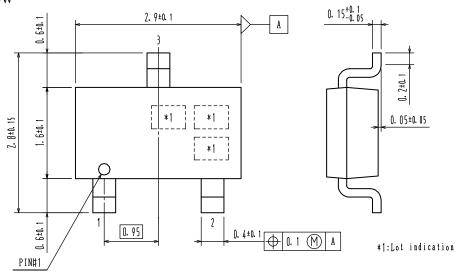
CASE 318BA ISSUE O

Unit: mm

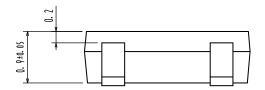
1: Gate

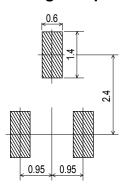
2: Source

3: Drain



Recommended Soldering Footprint





ORDERING INFORMATION

Device	Package	Shipping	Note
CPH3456-TL-H	CPH3, SC-59 SOT-23, TO-236	3,000	Pb-Free and
CPH3456-TL-W		pcs. / reel	Halogen Free

Note on usage: Since the CPH3456 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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